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December 2014

FCPF260N65FL1

N-Channel SuperFET® II FRFET® MOSFET

650 V, 15 A, 260 mΩ

Features

- 700 V @T_J = 150°C
- $R_{DS(on)} = 220 \text{ m}\Omega \text{ (Typ.)}$
- Ultra Low Gate Charge (Typ. Q_g = 46 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 223 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

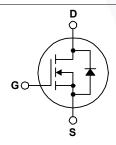
Applications

- LCD / LED / PDP TV Telecom / Server Power Supplies
- Solar Inverter
 AC DC Power Supply

Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SuperFET II FRFET® MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		FCPF260N65FL1	Unit	
V _{DSS}	Drain to Source Voltage		650	V
\ /	Cata ta Causaa Valtana	- DC	±20	V
V _{GSS} Gate to So	Gate to Source Voltage	- AC (f > 1 Hz	±30	V
	Drain Current	- Continuous (T _C = 25°C)	15	^
Drain Current	- Continuous (T _C = 100°C)	9.5	A	
I _{DM}	Drain Current	- Pulsed (Note 1	45	Α
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		293	mJ
I _{AR}	Avalanche Current (Note 1)		3	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		0.36	mJ
ما (ماد	MOSFET dv/dt		100	1//
dv/dt	Peak Diode Recovery dv/dt	(Note 3	50	V/ns
D	Davies Dissination	$(T_C = 25^{\circ}C)$	36	W
P_{D}	Power Dissipation	- Derate Above 25°C	0.29	W/°C
T _J , T _{STG}	Operating and Storage Temperation	-55 to +150	°C	
TL	Maximum Lead Temperature for	Soldering, 1/8" from Case for 5 Seconds	300	°C

Thermal Characteristics

Symbol	Parameter FCPF260N65FL1			
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.5	°C/W	
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient, Max. 62.5		*C/VV	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCPF260N65FL1	FCPF260N65F	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
D\/	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}, T_J = 25^{\circ}\text{C}$	650	-	-	V
BV _{DSS}	Dialii to Source Breakdown voltage	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}, T_J = 150^{\circ}\text{C}$	700	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 10 mA, Referenced to 25°C	-	0.72	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 650 V, V _{GS} = 0 V	-	-	10	
I _{DSS}	Zero Gate voltage Drain Current	$V_{DS} = 520 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	40	-	μА
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	μΑ

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 1.5 \text{ mA}$	3	-	5	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 7.5 \text{ A}$	-	220	260	mΩ
9 _{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_{D} = 7.5 \text{ A}$	ı	14.2	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 400 V V 0 V	-	1760	2340	pF
C _{oss}	Output Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz		59	80	pF
C _{rss}	Reverse Transfer Capacitance			1.0	-	pF
Coss	Output Capacitance	V _{DS} = 380 V, V _{GS} = 0 V, f = 1 MHz	- \	34	-	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V		223	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 380 V, I _D = 7.5 A,	-	46	60	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	9.6	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	20	-	nC
ESR	Equivalent Series Resistance	f = 1 MHz	-	0.52	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		- /	21.7	54	ns
t _r		$V_{DD} = 380 \text{ V}, I_D = 7.5 \text{ A},$	-/	10.5	32	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_g = 4.7 \Omega$	<i>j</i> -	54	118	ns
t _f	Turn-Off Fall Time	(Note 4)	/ -	5.8	22	ns

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diod	Maximum Continuous Drain to Source Diode Forward Current			15	Α
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-	45	Α
V_{SD}	Drain to Source Diode Forward Voltage V _{GS} = 0 V, I _{SD} = 7.5 A		-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 7.5 A,	-	98	- ,	ns
Q _{rr}	Reverse Recovery Charge $dI_F/dt = 100 A/\mu s$		-	450	-	nC

Notes:

- 1. Repetitive rating: pulse width limited by maximum junction temperature.
- 2. I_{AS} = 3 A, R_{G} = 25 Ω , Starting T_{J} = 25°C
- 3. I $_{SD} \leq 7.5$ A, di/dt ≤ 200 A/µs, V $_{DD} \leq 380$ V, Starting T $_{J}$ = $25^{\circ}C$
- 4. Essentially independent of operating temperature.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

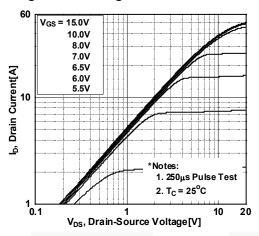


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

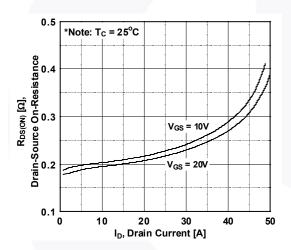


Figure 5. Capacitance Characteristics

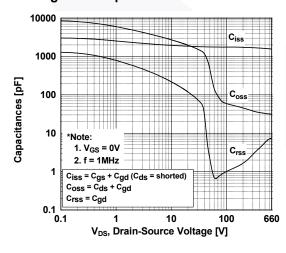


Figure 2. Transfer Characteristics

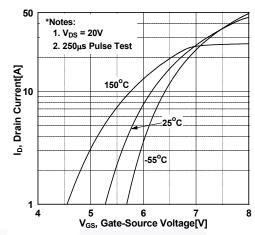


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

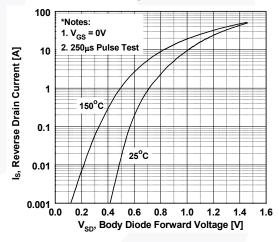
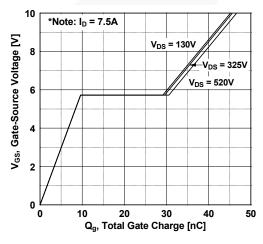


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

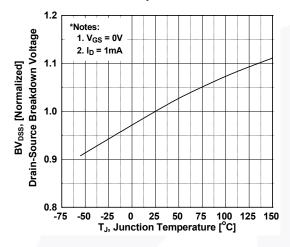


Figure 9. Maximum Safe Operating Area

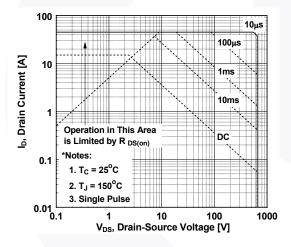


Figure 11. Eoss vs. Drain to Source Voltage

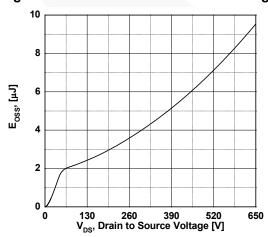


Figure 8. On-Resistance Variation vs. Temperature

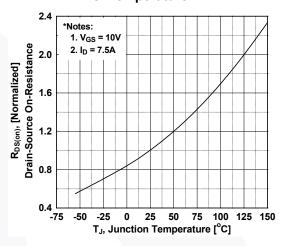
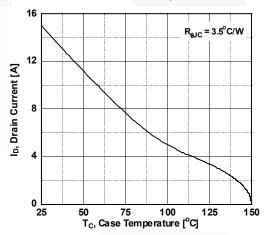
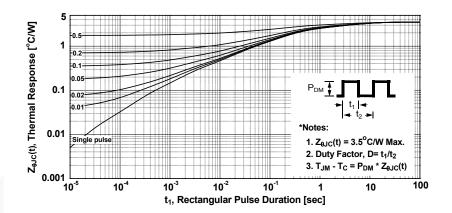


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



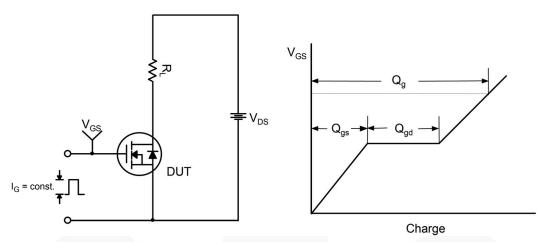


Figure 13. Gate Charge Test Circuit & Waveform

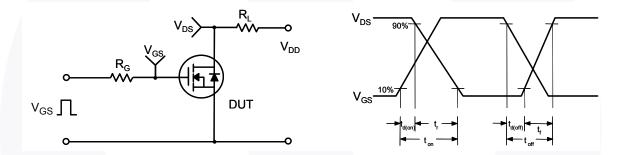


Figure 14. Resistive Switching Test Circuit & Waveforms

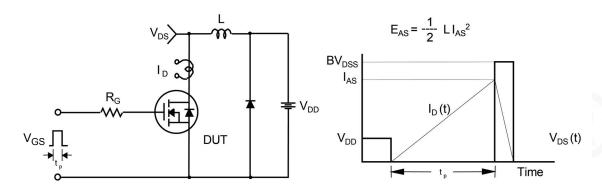


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

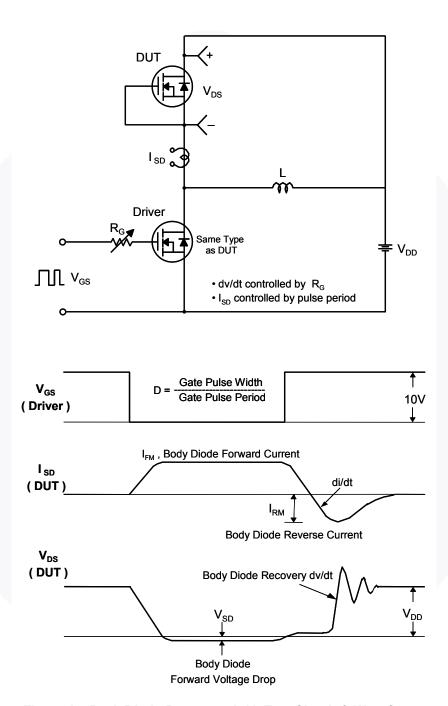


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

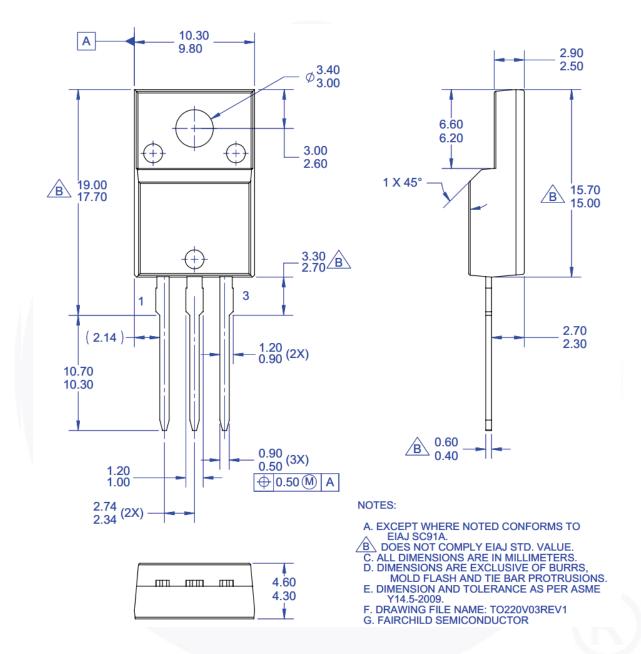


Figure 17. TO220, Molded, 3LD, Full Pack, EIAJ SC91, Takcheong

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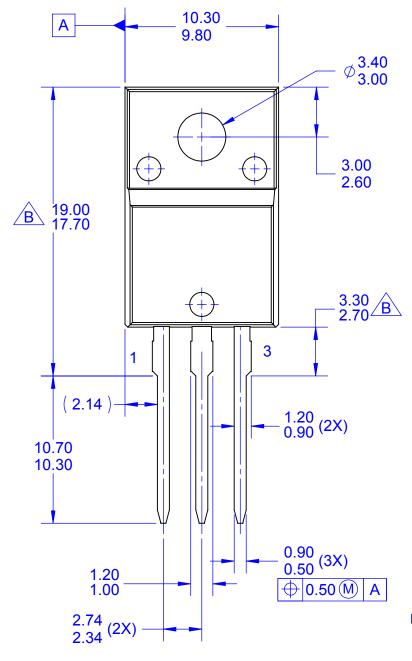
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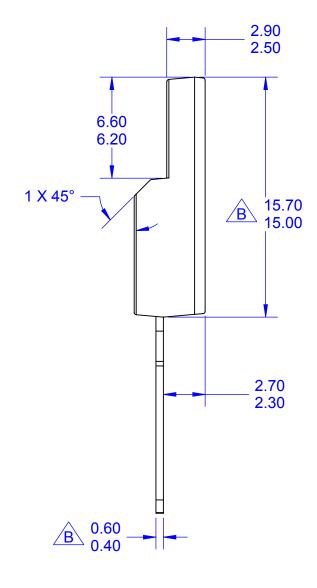
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Datasheet Identification	Product Status	Definition
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